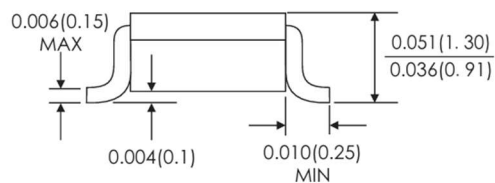
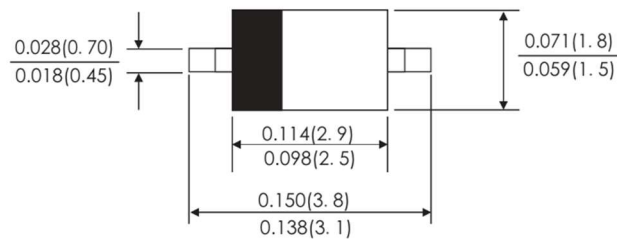


## SWITCHING DIODE

### Features

- For surface mounted applications
- Silicon epitaxial planar diode
- Fast switching diode
- Ideal for automated placement
- 350mW power dissipation

### SOD-123



Dimensions in inches and (millimeters)

### Absolute Maximum Ratings (T<sub>A</sub>=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	100	V
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	100	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	75	V
Average Rectified	I <sub>O</sub>	150	mA
Forward Continuous Current	I <sub>FM</sub>	300	mA
Non-Repetitive Peak Forward Surge Current ( t =1.0μs )	I <sub>FSM</sub>	2	A
Power Dissipation	P <sub>D</sub>	350	mW
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

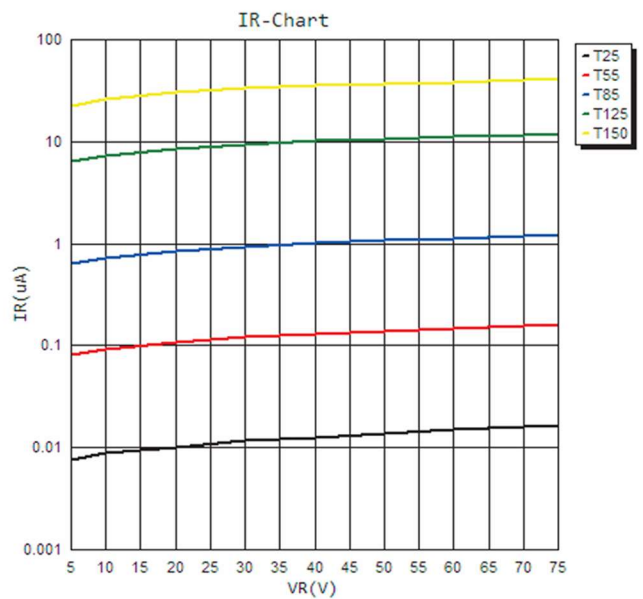
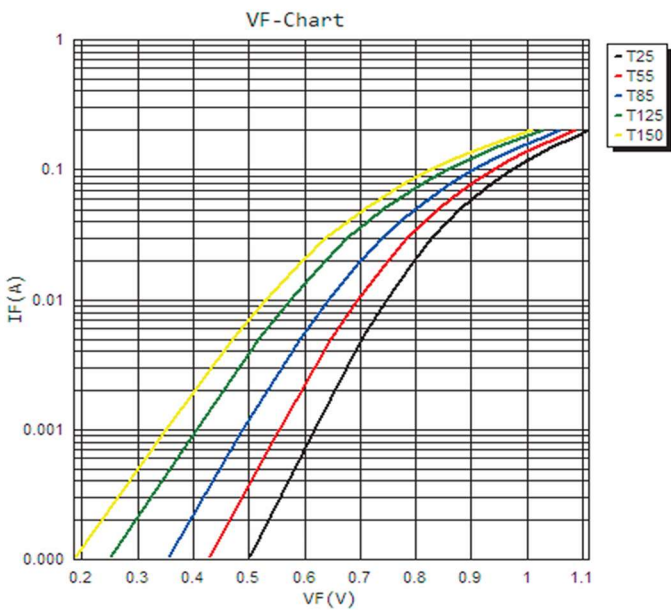
**Electrical Characteristics (TA=25°C, unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Max	Unit
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 20V, (25°C)		0.025	μA
		V <sub>R</sub> = 75V, (25°C)		1	
		V <sub>R</sub> = 75V, (150°C)		50	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 1mA		0.715	V
		I <sub>F</sub> = 10mA		0.855	
		I <sub>F</sub> = 50mA		1	
		I <sub>F</sub> = 150mA		1.25	
Capacitance	C <sub>T</sub>	V <sub>R</sub> =0, f=1MHZ		2	pF
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> =10mA, I <sub>RR</sub> =1mA I <sub>R</sub> =10mA, R <sub>L</sub> =100Ω		4	ns

**RATINGS AND CHARACTERISTIC CURVES**

FIG.1-FORWARD CHARACTERISTICS

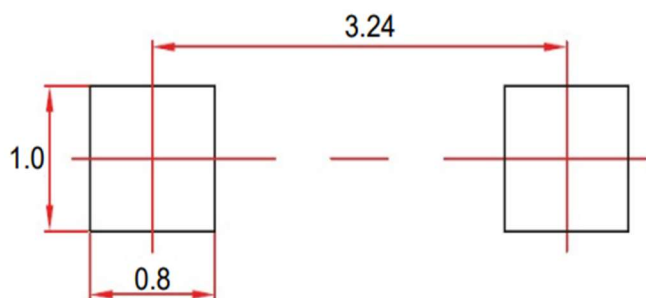
FIG.2-REVERSE CHARACTERISTICS



## Order Information

Part Number	Package	Marking	Quantity
1N4148W	SOD-123	T4	3000

## Suggested Pad Layout



### Note:

1. Dimension: mm
2. General tolerance:  $\pm 0.05$  mm
3. The pad layout is for reference purpose only